

Optocoupler, Phototriac Output, 400 V V_{DRM}

Features

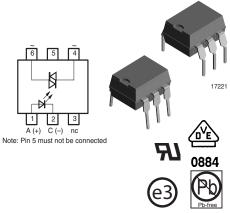
- Isolation materials according to UL 94-VO
- Pollution degree 2 (DIN/VDE 0110 resp. IEC 60664)
- Climatic classification 55/100/21 (IEC 60068 part 1)
- Special construction: Therefore, extra low coupling capacity of typical 0.2 pF, high Common Mode Rejection
- I_{FT} offered into 4 groups
- Rated impulse voltage (transient overvoltage)
 V_{IOTM} = 6 kV peak
- Isolation test voltage (partial discharge test voltage) V_{pd} = 1.6 kV
- Rated isolation voltage (RMS includes DC)
 V_{IOWM} = 600 V_{RMS} (848 V peak)
- Rated recurring peak voltage (repetitive)
 V_{IORM} = 600 V_{RMS}
- Thickness through insulation ≥ 0.75 mm
- Creepage current resistance according to VDE 0303/IEC 60112 Comparative Tracking Index: CTI = 275
- · Lead-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

Agency Approvals

- UL1577, File No. E76222 System Code C, Double Protection
- BSI: BS EN 41003, BS EN 60095 (BS 415), BS EN 60950 (BS 7002), Certificate number 7081 and 7402
- DIN EN 60747-5-2 (VDE0884)
 DIN EN 60747-5-5 pending
- FIMKO (SETI): EN 60950, Certificate No. 12398

Applications

Monitors
Air conditioners
Line Switches
Solid state relay
Microwave



Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):

- For appl. class I IV at mains voltage ≤ 300 V
- For appl. class I III at mains voltage \leq 600 V according to DIN EN 60747-5-2(VDE0884)/ DIN EN 60747-5-5 pending, table 2, suitable for.

Order Information

Part	Remarks
K3020P	I _{FT} < 30 mA, V _{DRM} = 400 V, DIP-6 300 mil
K3021P	I _{FT} < 15 mA, V _{DRM} = 400 V, DIP-6 300 mil
K3022P	I _{FT} < 10 mA, V _{DRM} = 400 V, DIP-6 300 mil
K3023P	I _{FT} < 5 mA, V _{DRM} = 400 V, DIP-6 300 mil
K3036P	I _{FT} < 3.6 mA, V _{DRM} = 400 V, DIP-6 300 mil
K3020PG	I _{FT} < 30 mA, V _{DRM} = 400 V, DIP-6 400 mil
K3021PG	I _{FT} < 15 mA, V _{DRM} = 400 V, DIP-6 400 mil
K3022PG	I _{FT} < 10 mA, V _{DRM} = 400 V, DIP-6 400 mil
K3023PG	I _{FT} < 5 mA, V _{DRM} = 400 V, DIP-6 400 mil
K3036PG	I _{FT} < 3.6 mA, V _{DRM} = 400 V, DIP-6 400 mil

G = Leadform 10.16 mm; G is not marked on the body

Description

The K3020P/ K3020PG series consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6-lead plastic dual inline package.

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VDE Standards

These couplers perform safety functions according to the following equipment standards:

DIN EN 60747-5-2(VDE0884)/ DIN EN 60747-5-5 pending

Optocoupler for electrical safety requirements

IEC 60950/EN 60950

Office machines (applied for reinforced isolation for mains voltage \leq 400 VRMS)

VDE 0804

Telecommunication apparatus and data processing **IEC 60065**

Safety for mains-operated electronic and related household apparatus.

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

Input

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V _R	5	V
Forward current		I _F	80	mA
Forward surge current	t _p ≤ 10 μs	I _{FSM}	3	A
Power dissipation		P _{diss}	100	mW
Junction temperature		Tj	100	°C

Output

Parameter	Test condition	Symbol	Value	Unit
Off state output terminal voltage		V_{DRM}	400	V
On state RMS current		I _{TRM}	100	mA
Peak surge current, non- repetitive	$t_p \le 10 \text{ ms}$	I _{TSM}	1.5	A
Power dissipation		P _{diss}	300	mW
Junction temperature		Tj	100	°C

Coupler

Parameter	Test condition	Symbol	Value	Unit
Isolation test voltage (RMS)		V _{ISO} 1)	3750	V _{RMS}
Total power dissipation		P _{tot}	350	mW
Ambient temperature range		T _{amb}	- 40 to + 85	°C
Storage temperature range		T _{stg}	- 55 to + 100	°C
Soldering temperature	2 mm from case, $t \le 10 \text{ s}$	T _{sld}	260	°C

¹⁾ Related to standard climate 23/50 DIN 50014

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Electrical Characteristics

 T_{amb} = 25 °C, unless otherwise specified

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

Input

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Forward voltage	I _F = 50 mA	V_{F}		1.25	1.6	V
Junction capacitance	V _R = 0, f = 1 MHz	C _j		50		pF

Output

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Forward peak off-state voltage (repetitive)	I _{DRM} = 100 nA	V _{DRM} ¹⁾	400			V
Peak on-state voltage	I _{TM} = 100 mA	V_{TM}		1.5	3	V
Critical rate of rise of off-state voltage	I _{FT} = 0, I _{FT} = 30 mA	dV/dt _{cr}		10		V/μs
		dV/dt _{crq}	0.1	0.2		V/μs

¹⁾ Test voltage must be applied within dv/dt ratings

Coupler

Parameter	Test condition	Part	Symbol	Min	Тур.	Max	Unit
Emitting diode trigger current	$V_{S} = 3 \text{ V}, R_{L} = 150 \Omega$	K3020P	I _{FT}		15	30	mA
		K3020PG	I _{FT}		15	30	mA
		K3021P	I _{FT}		8	15	mA
		K3021PG	I _{FT}		8	15	mA
		K3022P	I _{FT}		5	10	mA
		K3022PG	I _{FT}		5	10	mA
		K3023P	I _{FT}		2	5	mA
		K3023PG	I _{FT}		2	5	mA
		K3036P	I _{FT}		2	3.6	mA
		K3036PG	I _{FT}		2	3.6	mA
Holding current	$I_F = 10 \text{ mA}, V_S \ge 3 \text{ V}$		I _H		100		μΑ

Note: $\ensuremath{I_{\text{FT}}}$ is defined as a minimum trigger current

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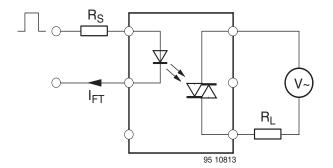
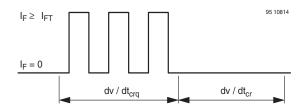


Figure 1. Test circuit for dV/dt_{cr} and dV/dt_{crq}



dv/dt_{cr} Highest value of the "rate of rise of off-state voltage" which does not cause any switching from the off-state to the on-state

dv/dt_{crq} Highest value of the "rate of rise of communicating voltage" which does not switch on the device again, after the voltage has decreased to zero and the trigger current is switched from I_{FT} to zero

Figure 2.

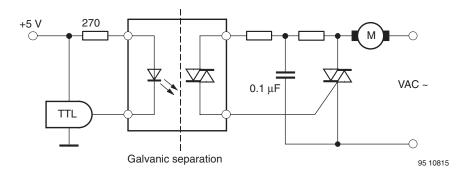


Figure 3. Motor control circuit

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Maximum Safety Ratings

(according to DIN EN 60747-5-2(VDE0884)/ DIN EN 60747-5-5 pending) see figure 1

This optocoupler is suitable for safe electrical isolation only within the safety ratings.

Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

Input

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Forward current		I _F			130	mA

Output

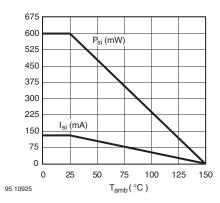
Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Power dissipation		P _{diss}			600	mW

Coupler

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Rated impulse voltage		V _{IOTM}			6	kV
Safety temperature		T _{si}			150	°C

Insulation Rated Parameters

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Partial discharge test voltage - Routine test	100 %, t _{test} = 1 s	V _{pd}	1.6			kV
Partial discharge test voltage - Lot test (sample test)	$t_{Tr} = 60 \text{ s}, t_{test} = 10 \text{ s},$ (see figure 5)	V _{IOTM}	6			kV
		V_{pd}	1.3			kV
Insulation resistance	V _{IO} = 500 V	R _{IO}	10 ¹²			Ω
	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	10 ¹¹			Ω
	V _{IO} = 500 V, T _{amb} = 150 °C (construction test only)	R _{IO}	10 ⁹			Ω





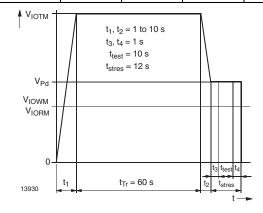


Figure 5. Test pulse diagram for sample test according to DIN EN 60747-5-2(VDE0884)/ DIN EN 60747-; IEC60747

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Typical Characteristics (Tamb = 25 °C unless otherwise specified)

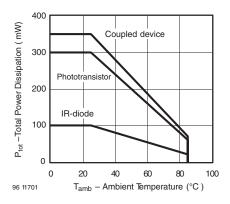


Figure 6. Total Power Dissipation vs. Ambient Temperature

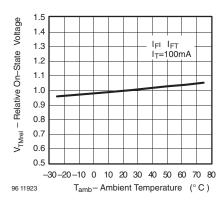


Figure 9. Relative On - State vs. Ambient Temperature

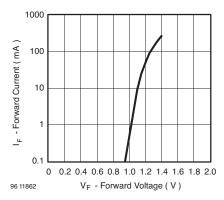


Figure 7. Forward Current vs. Forward Voltage

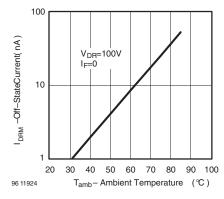


Figure 10. Off - State Current vs. Ambient Temperature

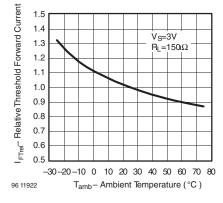


Figure 8. Relative Threshold Forward Current vs. Ambient Temperature

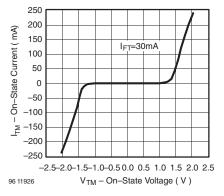
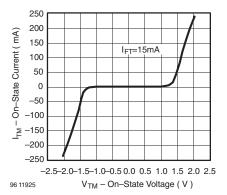


Figure 11. On - State Current vs. Ambient Temperature

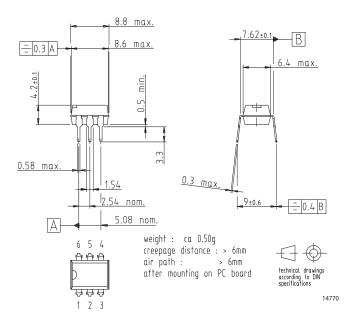


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Figure 12. On - State Current vs. Ambient Temperature



Package Dimensions in mm

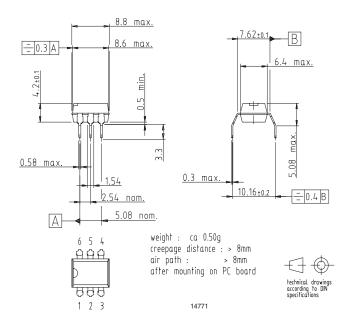


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Package Dimensions in mm



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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively. Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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